Preferred Device

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	75	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	600	mAdc

THERMAL CHARACTERISTICS

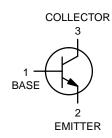
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^{\circ}C$	P _D	150	mW
Thermal Resistance Junction-to-Ambient	R_{\thetaJA}	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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MARKING DIAGRAM



P1 = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2222AWT1	SC-70	3000/Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

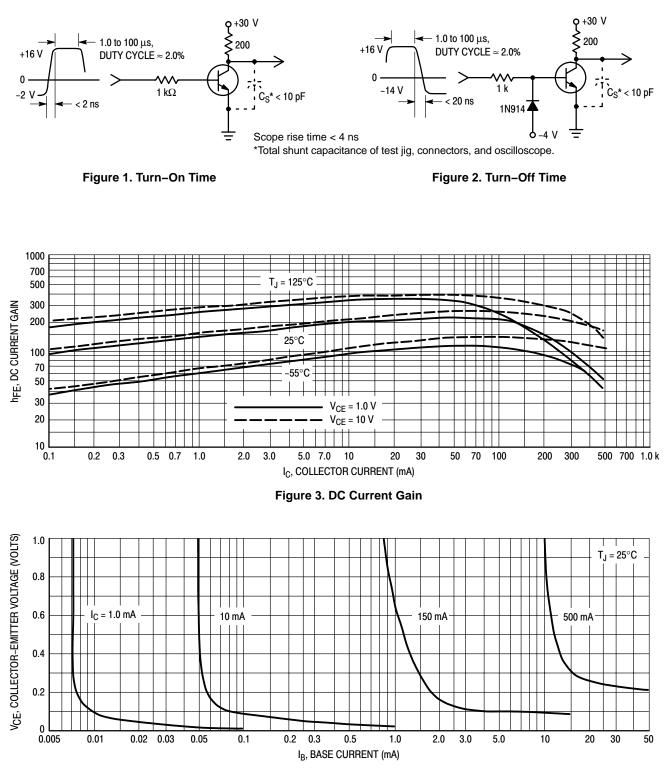
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Cha	racteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	(Note 1)	V _{(BR)CEO}	40	-	Vdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	75	-	Vdc	
$\begin{array}{l} \mbox{Emitter-Base Breakdown Voltage} \\ (I_E = 10 \ \mu \mbox{Adc}, \ I_C = 0) \end{array}$		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	-	20	nAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	-	10	nAdc	
ON CHARACTERISTICS (Note 1)					•
$ DC Current Gain (Note 1) \\ (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 10 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 150 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 500 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 500 mAdc, V_{CE} = 10 Vdc) \\ $		H _{FE}	35 50 75 100 40	- - - 300 -	-
$ Collector - Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc) \\ (I_C = 500 mAdc, I_B = 50 mAdc) $	V _{CE(sat)}	-	0.3 1.0	Vdc	
$\begin{array}{l} \text{Base}-\text{Emitter Saturation Voltage (Not}\\ (I_{C}=150 \text{ mAdc}, I_{B}=15 \text{ mAdc})\\ (I_{C}=500 \text{ mAdc}, I_{B}=50 \text{ mAdc}) \end{array}$	V _{BE(sat)}	0.6	1.2 2.0	Vdc	
SMALL-SIGNAL CHARACTERIS	TICS				•
Current-Gain – Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 10	0 MHz)	f _T	300	-	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)		C _{obo}	-	8.0	pF
Input Capacitance $(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ibo}	-	30	pF	
Input Impedance $(V_{CE} = 10 \text{ Vdc}, I_C = 10 \text{ mAdc}, f = 1.$	h _{ie}	0.25	1.25	k ohms	
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)		h _{re}	-	4.0	X 10 ⁻⁴
Small-Signal Current Gain (V_{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)		h _{fe}	75	375	-
Output Admittance (V_{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)		h _{oe}	25	200	μmhos
Noise Figure (V_{CE} = 10 Vdc, I _C = 100 μ Adc, R _S = 1.0 kΩ, f = 1.0 kHz)		NF	-	4.0	dB
SWITCHING CHARACTERISTICS	3			-	
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	_	10	

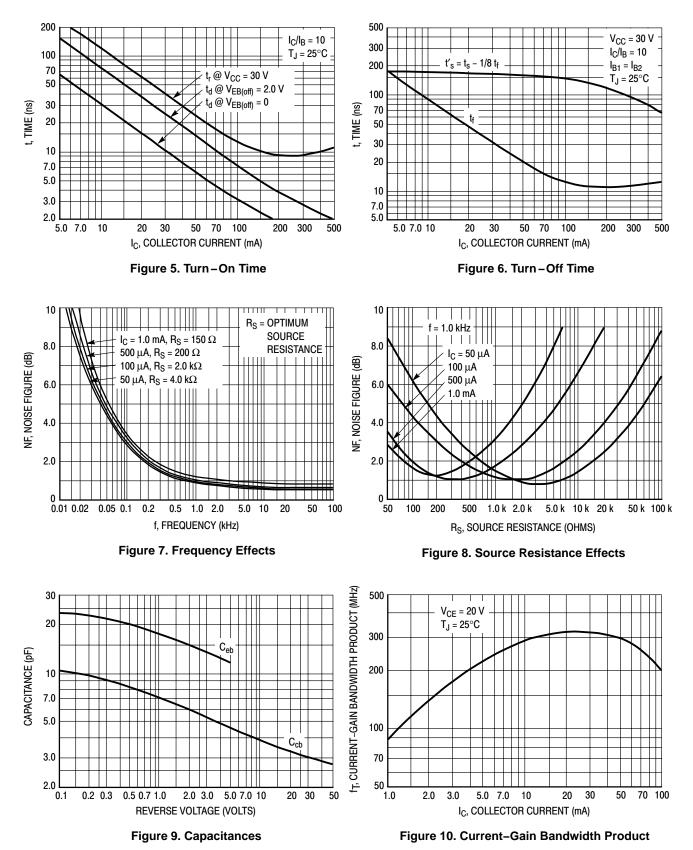
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	-	10	20
Rise Time	I _C = 150 mAdc, I _{B1} = 15 mAdc)	t _r	_	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t _s	-	225	20
Fall Time	I _{B1} = I _{B2} = 15 mAdc)	t _f	-	60	ns

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS







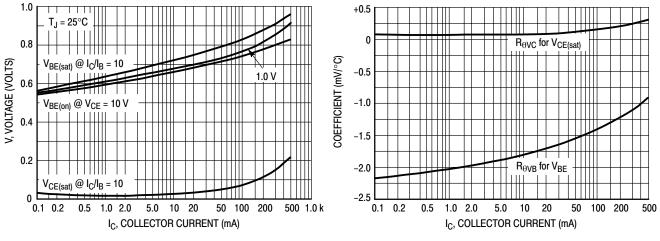
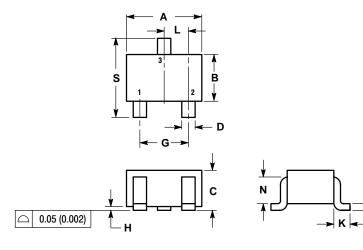


Figure 11. "On" Voltages

Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

SC-70/SOT-323 CASE 419-04 ISSUE L



NOTES:

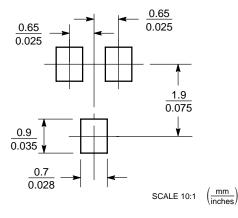
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.032	0.040	0.80	1.00	
D	0.012	0.016	0.30	0.40	
G	0.047	0.055	1.20	1.40	
Н	0.000	0.004	0.00	0.10	
J	0.004	0.010	0.10	0.25	
K	0.017	0.017 REF 0.425 REF		REF	
L	0.026 BSC		0.650	0 BSC	
N	0.028	0.028 REF		REF	
S	0.079	0.095	2.00	2.40	



SOLDERING FOOTPRINT



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